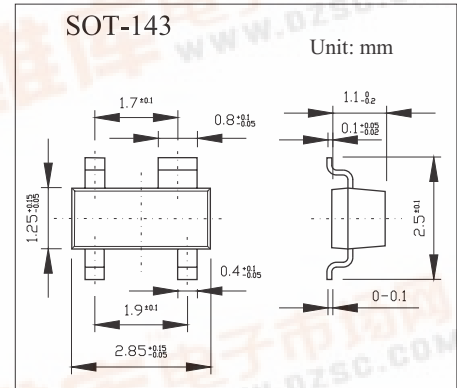


SMD Type Diodes

Silicon PIN Diodes
BAR60;BAR61

■ Features

- RF switch
- RF attenuator for frequencies above 10 MHz



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	100	V
Forward current	I _F	140	mA
Total power dissipation, T _s ≤ 65°C (Note 1)	P _{tot}	250	mW
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55 to +150	°C
Operating temperature range	T _{op}	-55 to +150	°C
Junction - ambient ⁽¹⁾	R _{th JA}	≤ 580	K/W
Junction - soldering point	R _{th JS}	≤ 340	K/W

Note

1. Unit Rating. Total Rating = Unit Rating × 1.5

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I _R	V _R = 50 V			100	nA
		V _R = 100 V			1	μA
Forward voltage	V _F	I _F = 100 mA			1.25	V
Diode capacitance	C _T	V _R = 50 V, f = 1 MHz		0.25	0.5	pF
		V _R = 0, f = 100 MHz		0.2		
Zero bias conductance	g _p	V _R =0 V, f=100 MHz		50		μS
Charge carrier life time	τ _L	I _F = 10 mA, I _R = 6 mA		1		μS
Differential forward resistance	r _f	f = 100 MHz, I _F = 0.01 mA		2800		Ω
		I _F = 0.1 mA		380		
		I _F = 1.0 mA		45		
		I _F = 10 mA		7		

■ Marking

Type	BAR60	BAR61
Marking	60	61

